

Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) [[1.]] A switching arrangement for the controlled parallel switching of a first energy- storing electrolytic condenser (C1) with a second energy-storing electrolyte condenser (C2) in response to a switching signal supplied to a control input (VS), said first electrolytic condenser (C1) has a capacity of at least 500 μ F; said second electrolytic condenser has a likewise large capacity, the switching arrangement comprises an electronic switch formed by the main circuit of a semiconductor device being a field effect transistor (FT) with a gate electrode connected through an RC-type delay member to the control input (VS); wherein for protecting both the field effect transistor (FT) and the connected electrolytic condensers (C1, C2) from the damaging effect of current surges appearing as switching transients but which, at the same time, affects the switching process only to the extent necessary for the protection, the rising of the current in said main circuit is delayed, wherein the delay is provided by two delay members, the first delay member is constituted by said RC-type delay member, the second delay member being an inductive element (L) connected in the main circuit of the field effect transistor (FT), the inductive element (L) ~~has a very low ohmic resistance and being~~ is constituted by a conductor (10) of predetermined length surrounded by a high-frequency ferrite core (11, 12); the delay effected by the RC member ensures only a fraction of the full switching delay.

2. (Previously Presented) The switching arrangement as defined in claim 1, wherein the ferrite core (11, 12) has two bores which are at a predetermined distance from one another and which have parallel axes; the conductor (10) has two legs passed through the bores.

3. (Previously Presented) The switching arrangement as defined in claim 2, wherein it comprises a plurality of short, stacked ferrite cores (11).

4. (Previously Presented) The switching arrangement as defined in claim 1, wherein in the RC member the capacitive element is formed by the input capacity of the field effect transistor (FT) and the unavoidable scattered capacities.

5. (Currently Amended) The switching arrangement as defined in claim 1, ~~(Currently Amended)~~ wherein the capacity of the switched electrolytic condensers is in the range of 10,000 μF .

6. (New) A switching arrangement for the controlled connecting in parallel of a first energy- storing electrolytic condenser with a second energy-storing electrolyte condenser in response to a switching signal supplied to a control input, said first electrolytic condenser has a capacity of at least 500 μF ; said second electrolytic condenser has a likewise large capacity, with the first and second condensers each having one terminal connected to a common terminal for a source of variable voltage, and a second terminal connected to ground, and the switching arrangement comprises an electronic switch connected between the second terminal of the second condenser and ground and formed by the main circuit of a semiconductor field effect transistor having a gate electrode connected through an RC-type delay member to a control input; and wherein for protecting both the field effect transistor and the connected electrolytic condensers from the damaging effect of current surges appearing as switching

transients but which, at the same time, affects the switching process only to the extent necessary for the protection, the rising of the current in said main circuit is delayed, wherein the delay is provided by two delay members, the first delay member is constituted by said RC-type delay member, and the second delay member being an inductive element connected in the main circuit of the field effect transistor, with the inductive element being a conductor of predetermined length surrounded by a ferrite core; the delay effected by the RC member ensuring only a fraction of the full switching delay.

7 (New) The switching arrangement as defined in claim 6, wherein the ferrite core is formed of a high-frequency ferrite material.